

IN THE CLAIMS

This listing of claims replaces all prior versions and listings of claims:

1. (Currently Amended) A solid-state imaging device comprising;

an imaging area having a plurality of unit cells in a two-dimensional array, each unit cell of the plurality of unit cells including a group of a predetermined number of pixels; ~~and~~ signal lines ~~used for selecting to select~~ the pixels, wherein ~~the each~~ unit cell includes a plurality of photoelectric converters corresponding to the pixels;

~~an amplifying unit means~~, shared by the pixels, ~~for amplifying to amplify~~ a signal read out ~~readout~~ from each photoelectric converter and ~~outputting output~~ the amplified ~~readout~~ signal; and

~~transfer means for selectively reading out the signal from the photoelectric converter and supplying a supply element to supply~~ the readout signal to the amplifying ~~means unit~~, and

wherein,

the signal line ~~used for driving to drive~~ the amplifying ~~means unit~~ is a full-face signal line shared by ~~all the~~ pixels and driving the full-face signal line allows the signal to be read out from each pixel, ~~and~~

the full-face signal line serves as a light shielding film and has an opening corresponding to a light receiving surface for every pixel.

2. (Currently Amended) The solid-state imaging device according to claim 1, further comprising;

~~a reset unit means for resetting to reset~~ an input section of the amplifying ~~means unit~~.

3. (Currently Amended) The solid-state imaging device according to claim 2, wherein the signal line ~~used for driving to drive~~ the reset ~~means unit~~ is the full-face signal line and driving the full-face signal line resets the input section of the amplifying ~~means unit~~.

4. (Withdrawn) The solid-state imaging device according to claim 1, wherein the unit cells are shifted from each other in the column direction by one pixel or by an amount smaller than one pixel for every pixel column in the imaging area.

5. (Currently Amended) The solid-state imaging device according to claim 2, wherein further comprising:

a full-face selection signal passing ~~that passes~~ through the full-face signal line used for driving to drive the reset means unit and the amplifying means unit.

wherein,

the full-face selection signal is changed from an active state to a non-active state at a time outside a readout operation period of the pixel.

6. (Currently Amended) The solid-state imaging device according to claim 2, wherein the reset means unit is a transistor, and

wherein a full-face selection signal passing through the full-face signal line is changed to an active state during a readout period of the pixel, a reset signal supplied to the gate of the reset means unit is changed to a non-active state, and a driving signal supplied to the a transfer means unit is changed to the active state to read out a charge signal stored in the photoelectric converter.

7. (Withdrawn) A solid-state imaging device comprising
an imaging area having a plurality of unit cells in a two-dimensional array, each unit cell including a group of a predetermined number of pixels; and
signal lines used for selecting the pixels,

wherein the unit cell includes a plurality of photoelectric converters corresponding to the pixels; amplifying means, shared by the pixels, for amplifying a signal read out from each

photoelectric converter and outputting the amplified signal; and

transfer means for selectively reading out the signal from the photoelectric converter and supplying the readout signal to the amplifying means, and

wherein the photoelectric converters in the unit cells are arranged so as to be diagonally adjacent to each other.

8. (Withdrawn) The solid-state imaging device according to claim 7, wherein the photoelectric converters diagonally adjacent to each other are horizontally or vertically shifted by an amount smaller than one pixel.

9. (Withdrawn) The solid-state imaging device according to claim 7, wherein the signal line used for driving the amplifying means is a full-face signal line shared by all the pixels and driving the full-face signal line allows the signal to be read out from each pixel.

10. (Withdrawn) The solid-state imaging device according to claim 9, further comprising reset means for resetting an input section of the amplifying means.

11. (Withdrawn) The solid-state imaging device according to claim 10, wherein the signal line used for driving the reset means is the full-face signal line and driving the full-face signal line resets the input section of the amplifying means.

12. (Withdrawn) The solid-state imaging device according to claim 7, wherein signals output from the pixels in the imaging area are read out through two output systems.

13. (Withdrawn) The solid-state imaging device according to claim 12, wherein the imaging area is provided with a RGB Bayer color filter, and wherein signals are read out from the pixels filtered by G filters through the same output system.

14. (Withdrawn) The solid-state imaging device according to claim 10, wherein a full-face selection signal passing through the full-face signal line used for driving the reset means and the amplifying means is changed from an active state to a non-active state at a time outside a readout operation period of the pixel.

15. (Withdrawn) The solid-state imaging device according to claim 10, wherein the reset means is a transistor, and wherein a full-face selection signal passing through the full-face signal line is changed to an active state during a readout period of the pixel, a reset signal supplied to the gate of the reset means is changed to a non-active state, and a driving signal supplied to the transfer means is changed to the active state to read out a charge signal stored in the photoelectric converter.

16. (Withdrawn) A solid-state imaging device comprising
an imaging area having a plurality of unit cells in a two-dimensional array, each unit cell including a group of a predetermined number of pixels,
wherein the unit cell includes an amplifying transistor that amplifies an electric charge read out from a photoelectric converter in each pixel;
a reset transistor that resets an input section of the amplifying transistor; and
a signal line that is connected to the reset transistor and varies a reset level of the amplifying transistor,
wherein at least two pixels in the unit cell share the amplifying transistor, and wherein the signal line is shared by all the pixels.

17. (Withdrawn) The solid-state imaging device according to claim 16, further comprising
output signal lines provided for every pixel column in the imaging area,
wherein each color of filter in a Bayer color filter is provided over the pixel,

wherein two pixels having a red filter and a blue filter provided thereover, the red filter being adjacent to the blue filter, share one output signal line, and

wherein two pixels having two adjacent green filters provided thereover share one output signal line.

18. (Withdrawn) The solid-state imaging device according to claim 17, further comprising

at least two horizontal signal lines corresponding to the multiple output signal lines, wherein signals are read out from all the pixels corresponding to the green filters in the color filter to the same horizontal signal line.

19. (Withdrawn) The solid-state imaging device according to claim 16, wherein a color filter is provided over the pixels,

wherein each pixel includes a transfer transistor that reads out the electric charge from the photoelectric converter, and

wherein the electric charge is read out from all the pixels corresponding to green filters in the color filter in the same direction by the transfer transistors.

20. (Withdrawn) The solid-state imaging device according to claim 16, wherein the signal line has an opening corresponding to the photoelectric converter and functions as a light shielding film.